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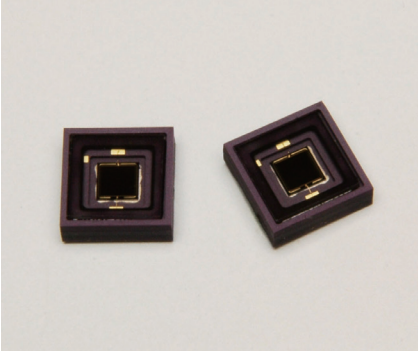
Two-color detector



K12729-010K

Wide spectral response range: 0.9 to 2.55 µm
Compact ceramic package

The K12729-010K is a two-color detector in a compact ceramic package, covering a wide spectral response range. Like the current K11908-010K, it incorporates two InGaAs PIN photodiodes with different spectral response, along the same optical axis. It features low noise and low dark current and supports reflow soldering.

Features

- **Wide spectral response range**
- **Compact, low noise, low dark current**
- **Supports reflow soldering**

Applications

- **Spectrophotometers**
- **Radiation thermometers**

Structure

Parameter	Symbol	Condition	Specification	Unit
Window material	-		Borosilicate glass	-
Package	-		Ceramic	-
Photosensitive area	-	InGaAs (λc=1.7 µm)	2.4 × 2.4	mm
		InGaAs (λc=2.55 µm)	ϕ1.0	

Absolute maximum ratings

Parameter	Symbol	Condition	Value	Unit
Reverse voltage	VR max	InGaAs (λc=1.7 µm), Ta=25 °C	2	V
		InGaAs (λc=2.55 µm), Ta=25 °C	1	
Operating temperature	Topr	No condensation*1	-20 to +70	°C
Storage temperature	Tstg	No condensation*1	-20 to +85	°C

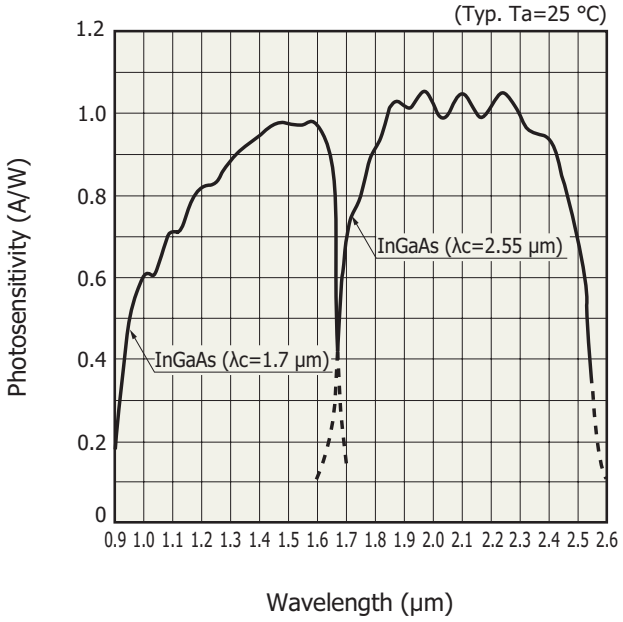
*1: When there is a temperature difference between a product and the surrounding area in high humidity environment, dew condensation may occur on the product surface. Dew condensation on the product may cause deterioration in characteristics and reliability.

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

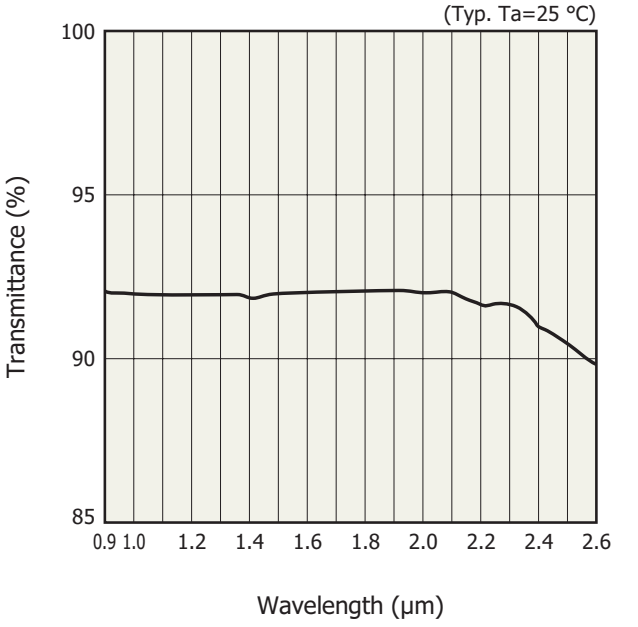
Electrical and optical characteristics (Ta=25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Spectral response range	λ	InGaAs (λc=1.7 μm)	-	0.9 to 1.7	-	μm
		InGaAs (λc=2.55 μm)	-	1.7 to 2.55	-	
Peak sensitivity wavelength	λp	InGaAs (λc=1.7 μm)	-	1.55	-	μm
		InGaAs (λc=2.55 μm)	-	2.1	-	
Photosensitivity	S	InGaAs (λc=1.7 μm), λ=λp	0.85	0.95	-	A/W
		InGaAs (λc=2.55 μm), λ=λp	0.7	1.0	-	
Dark current	ID	InGaAs (λc=1.7 μm), VR=10 mV	-	1	10	nA
		InGaAs (λc=2.55 μm), VR=10 mV	-	0.7	3.5	μA
Cutoff frequency	fc	InGaAs (λc=1.7 μm), -3 dB VR=0 V, RL=50 Ω	1	2	-	MHz
		InGaAs (λc=2.55 μm), -3 dB VR=0 V, RL=50 Ω	2	6	-	
Terminal capacitance	Ct	InGaAs (λc=1.7 μm), VR=0 V, f=1 MHz	-	1.5	2.5	nF
		InGaAs (λc=2.55 μm), VR=0 V, f=1 MHz	-	0.5	1	
Shunt resistance	Rsh	InGaAs (λc=1.7 μm), VR=10 mV	1	10	-	MΩ
		InGaAs (λc=2.55 μm), VR=10 mV	2.8	14	-	kΩ
Detectivity	D*	InGaAs (λc=1.7 μm), λ=λp	1×10^{12}	5×10^{12}	-	cm·Hz$^{1/2}$/W
		InGaAs (λc=2.55 μm), λ=λp	2×10^{10}	7×10^{10}	-	

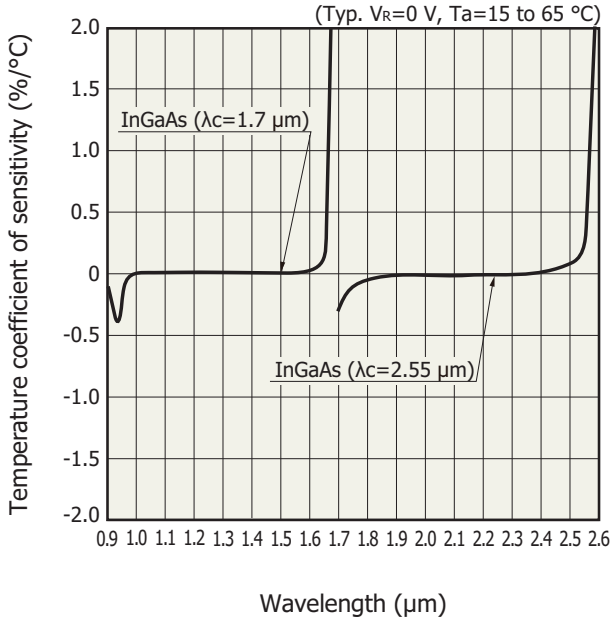
Spectral response



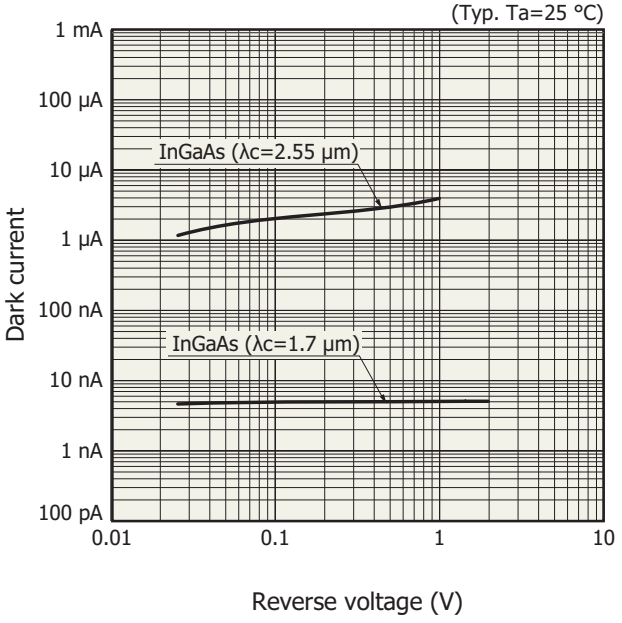
Spectral transmittance of window material



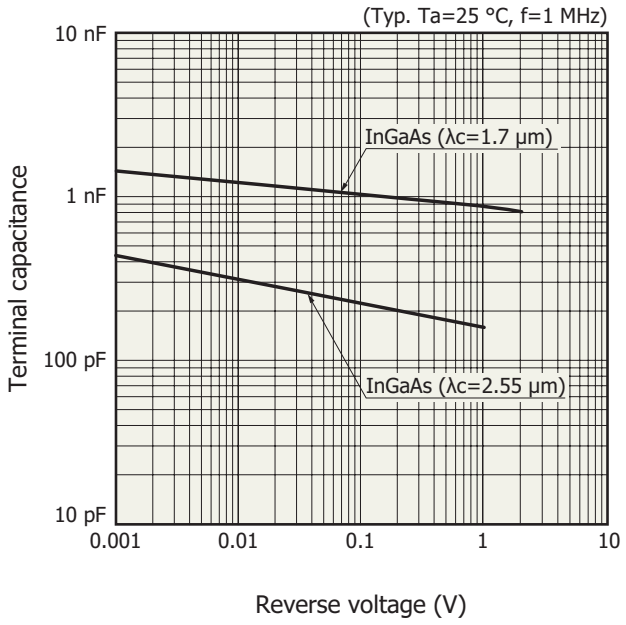
Temperature characteristics of sensitivity



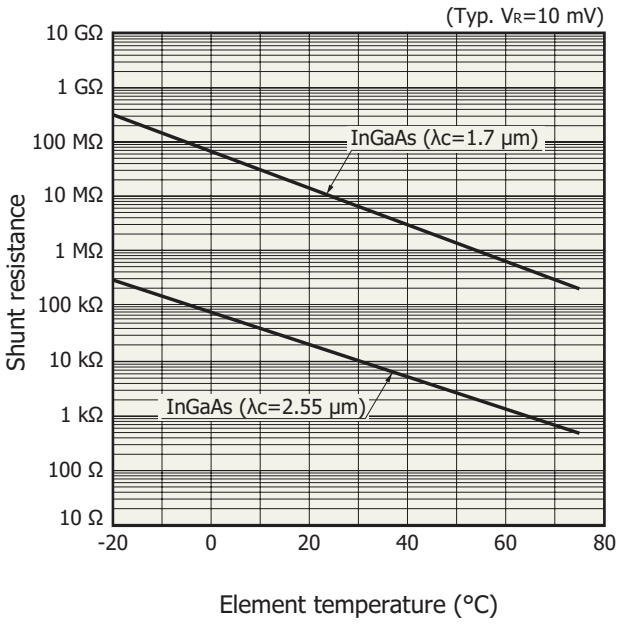
Dark current vs. reverse voltage



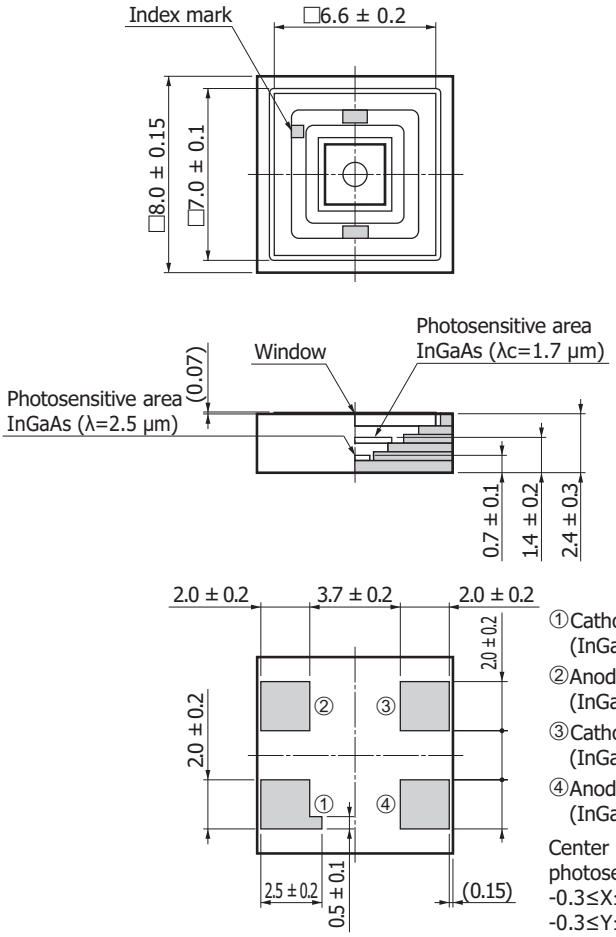
Terminal capacitance vs. reverse voltage



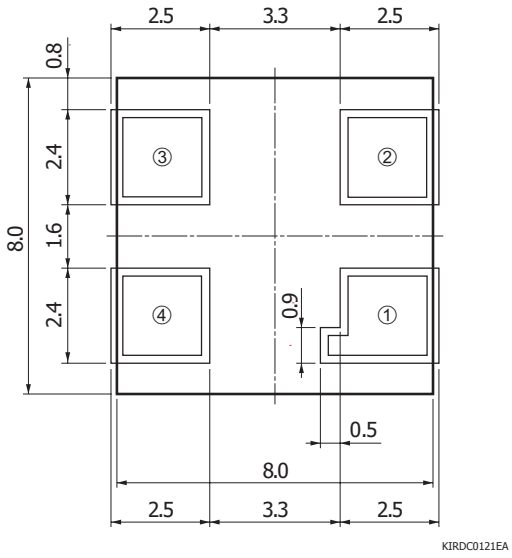
Shunt resistance vs. element temperature



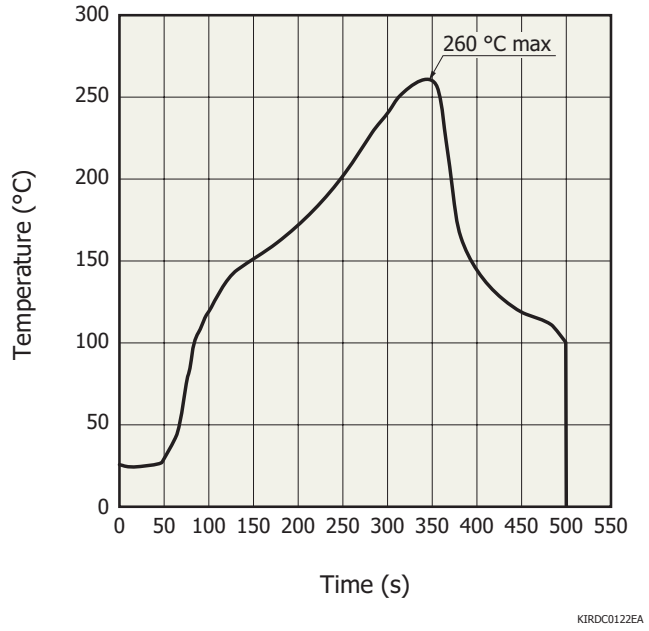
Dimensional outline (unit: mm)



Recommended land mark pattern (unit: mm)



Measured example of temperature profile with our hot-air reflow oven for product testing



KIRDC0122EA

· After unpacking, store the device in an environment at a temperature range of 5 to 30 °C and a humidity of 60% or less, and perform reflow soldering within 4 weeks.
· The thermal stress applied to the device during reflow soldering varies depending on the circuit board and the reflow oven that is used.
· When setting the reflow conditions, verify that the reliability of the device is not compromised by the reflow soldering process.

Related information

www.hamamatsu.com/sp/ssd/doc_en.html

■ Precautions
· Disclaimer
· Safety consideration
· Metal, ceramic, plastic package products

■ Technical information
· Infrared detectors

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